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# 2SC2611

Silicon NPN Triple Diffused

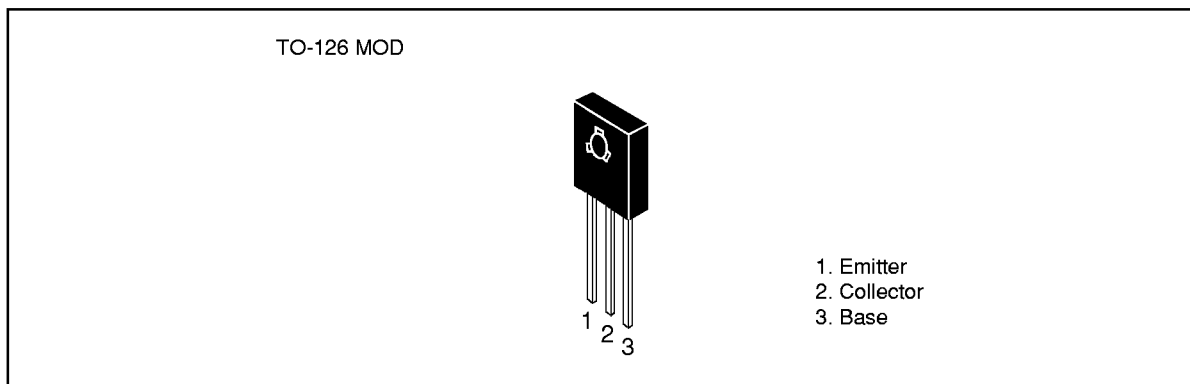
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### Application

High voltage amplifier TV VIDEO output

### Outline



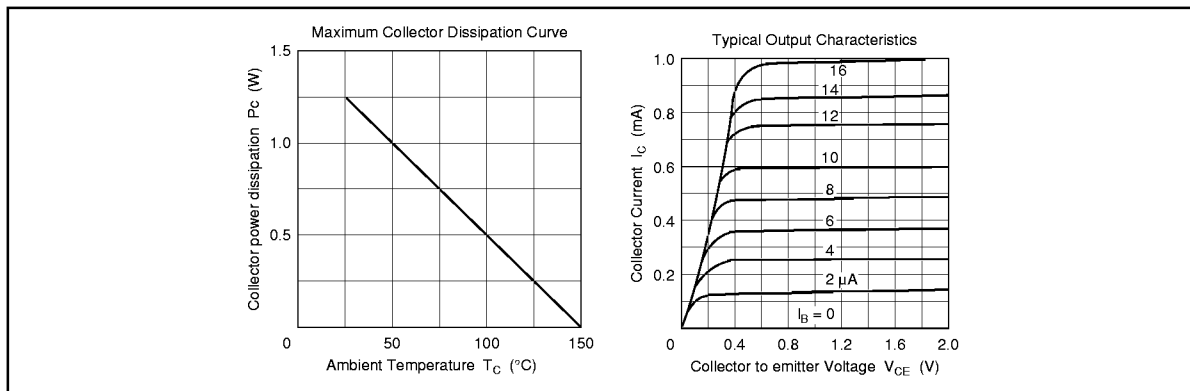
### Absolute Maximum Ratings (Ta = 25°C)

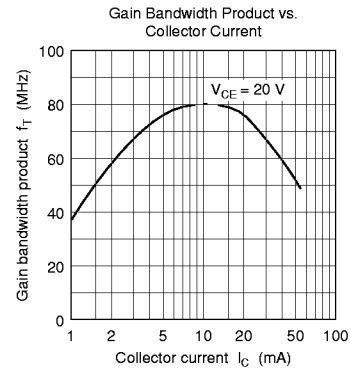
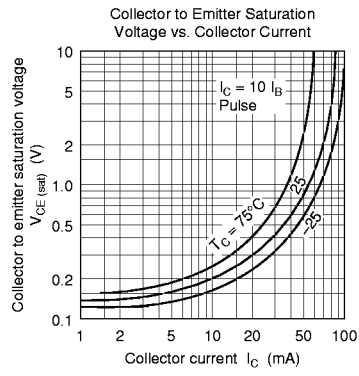
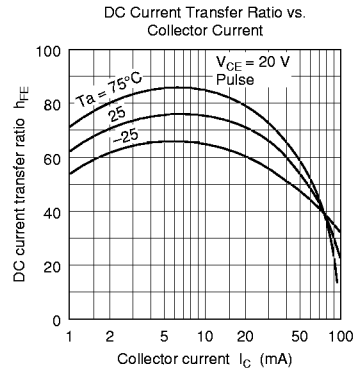
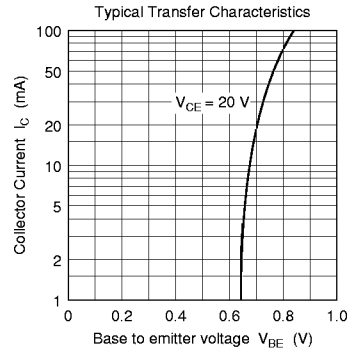
Item	Symbol	Rated	Unit
Collector to base voltage	$V_{CBO}$	300	V
Collector to emitter voltage	$V_{CEO}$	300	V
Emitter to base voltage	$V_{EBO}$	5	V
Collector current	$I_C$	100	mA
Collector power dissipation	$P_C$	1.25	W
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-55 to +150	°C

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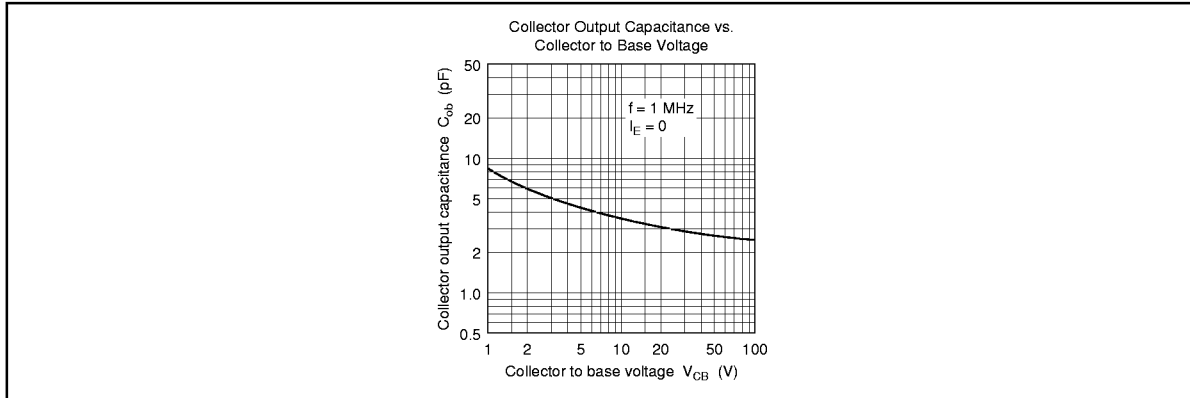
### Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	300	—	—	V	$I_C = 10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	300	—	—	V	$I_C = 1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	—	—	V	$I_E = 10 \mu A, I_C = 0$
Collector cutoff current	$I_{CEO}$	—	—	1.0	$\mu A$	$V_{CE} = 250 \text{ V}, R_{BE} = \infty$
DC current transfer ratio	$h_{FE}$	30	—	200		$V_{CE} = 20 \text{ V}, I_C = 20 \text{ mA}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	1.5	V	$I_C = 20 \text{ mA}, I_B = 2 \text{ mA}$
Gain bandwidth product	$f_T$	50	80	—	MHz	$V_{CE} = 20 \text{ V}, I_C = 20 \text{ mA}$
Collector output capacitance	Cob	—	—	4.0	pF	$V_{CB} = 20 \text{ V}, I_E = 0, f = 1 \text{ MHz}$





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